

# BUK652R6-40C

## N-channel TrenchMOS FET

Rev. 01 — 5 July 2010

Objective data sheet

## 1. Product profile

### 1.1 General description

Intermediate level gate drive N-channel enhancement mode Field-Effect Transistor (FET) in a plastic package using advanced TrenchMOS technology. This product has been designed and qualified to the appropriate AEC Q101 standard for use in high performance automotive applications.

### 1.2 Features and benefits

- AEC Q101 compliant
- Suitable for thermally demanding environments due to 175 °C rating
- Suitable for intermediate level gate drive sources

### 1.3 Applications

- 12 V Automotive systems
- Start-Stop micro-hybrid applications
- Electric (hydraulic) power steering
- Transmission control
- HVAC
- Ultra high performance power switching
- Motors, lamps and solenoid control

### 1.4 Quick reference data

Table 1. Quick reference data

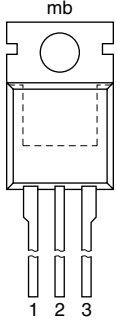
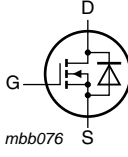
Symbol	Parameter	Conditions	Min	Typ	Max	Unit
$V_{DS}$	drain-source voltage	$T_j \geq 25\text{ °C}; T_j \leq 175\text{ °C}$	-	-	40	V
$I_D$	drain current	$V_{GS} = 10\text{ V}; T_{mb} = 25\text{ °C};$ see <a href="#">Figure 1</a>	[1]	-	100	A
$P_{tot}$	total power dissipation	$T_{mb} = 25\text{ °C};$ see <a href="#">Figure 2</a>	-	-	262	W
<b>Static characteristics</b>						
$R_{DS(on)}$	drain-source on-state resistance	$V_{GS} = 10\text{ V}; I_D = 15\text{ A};$ $T_j = 25\text{ °C};$ see <a href="#">Figure 5</a>	-	2.2	2.6	mΩ
<b>Avalanche ruggedness</b>						
$E_{DS(AL)S}$	non-repetitive drain-source avalanche energy	$I_D = 100\text{ A}; V_{sup} \leq 40\text{ V};$ $R_{GS} = 50\text{ }\Omega; V_{GS} = 10\text{ V};$ $T_{j(init)} = 25\text{ °C};$ unclamped	-	-	774	mJ

[1] Continuous current is limited by package.



## 2. Pinning information

Table 2. Pinning information

Pin	Symbol	Description	Simplified outline	Graphic symbol
1	G	gate		
2	D	Drain		
3	S	source		
mb	D	mounting base; connected to drain		

**SOT78 (TO-220AB)**

## 3. Ordering information

Table 3. Ordering information

Type number	Package		
	Name	Description	Version
BUK652R6-40C	TO-220AB	plastic single-ended package; heatsink mounted; 1 mounting hole; 3-lead TO-220AB	SOT78

## 4. Limiting values

**Table 4. Limiting values**

In accordance with the Absolute Maximum Rating System (IEC 60134).

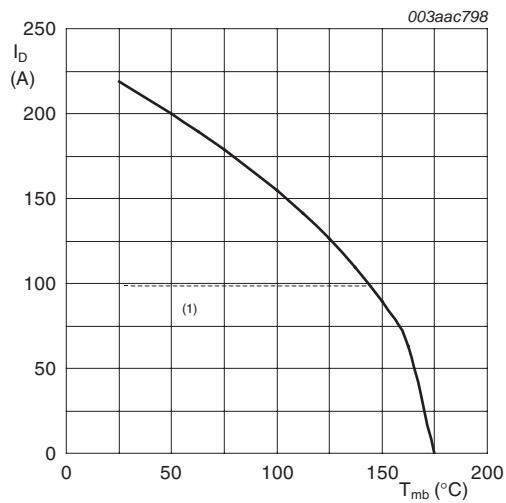
Symbol	Parameter	Conditions	Min	Typ	Max	Unit	
$V_{DS}$	drain-source voltage	$T_j \geq 25\text{ °C}; T_j \leq 175\text{ °C}$	-	-	40	V	
$V_{GS}$	gate-source voltage		-20	-	20	V	
$I_D$	drain current	$T_{mb} = 25\text{ °C}; V_{GS} = 10\text{ V};$ see <a href="#">Figure 1</a>	[1]	-	-	100	A
		$T_{mb} = 100\text{ °C}; V_{GS} = 10\text{ V};$ see <a href="#">Figure 1</a>	[1]	-	-	100	A
$I_{DM}$	peak drain current	$T_{mb} = 25\text{ °C}; t_p \leq 10\text{ }\mu\text{s};$ pulsed	-	-	878	A	
$P_{tot}$	total power dissipation	$T_{mb} = 25\text{ °C};$ see <a href="#">Figure 2</a>	-	-	262	W	
$T_{stg}$	storage temperature		-55	-	175	°C	
$T_j$	junction temperature		-55	-	175	°C	
<b>Source-drain diode</b>							
$I_S$	source current	$T_{mb} = 25\text{ °C}$	[1]	-	-	100	A
$I_{SM}$	peak source current	$t_p \leq 10\text{ }\mu\text{s};$ pulsed; $T_{mb} = 25\text{ °C}$	-	-	-	878	A
<b>Avalanche ruggedness</b>							
$E_{DS(AL)S}$	non-repetitive drain-source avalanche energy	$I_D = 100\text{ A}; V_{sup} \leq 40\text{ V};$ $R_{GS} = 50\text{ }\Omega; V_{GS} = 10\text{ V};$ $T_{j(init)} = 25\text{ °C};$ unclamped	-	-	-	774	mJ
$E_{DS(AL)R}$	repetitive drain-source avalanche energy		[2][3][4]	-	-	-	J

[1] Continuous current is limited by package.

[2] Single-pulse avalanche rating limited by maximum junction temperature of 175 °C.

[3] Repetitive avalanche rating limited by an average junction temperature of 170 °C.

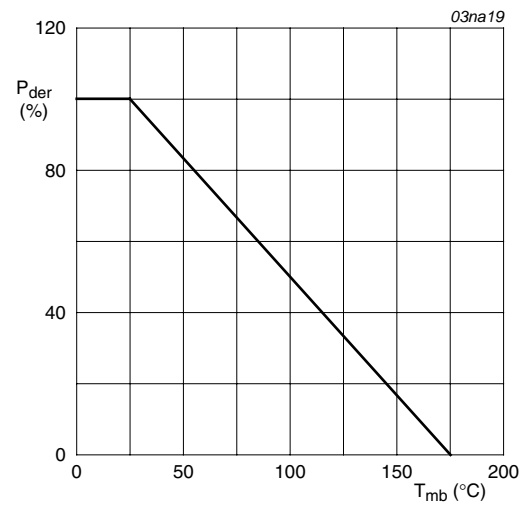
[4] Refer to application note AN10273 for further information.



$$V_{GS} \geq 10V$$

(1) Capped at 100 A due to package.

**Fig 1. Continuous drain current as a function of mounting base temperature**



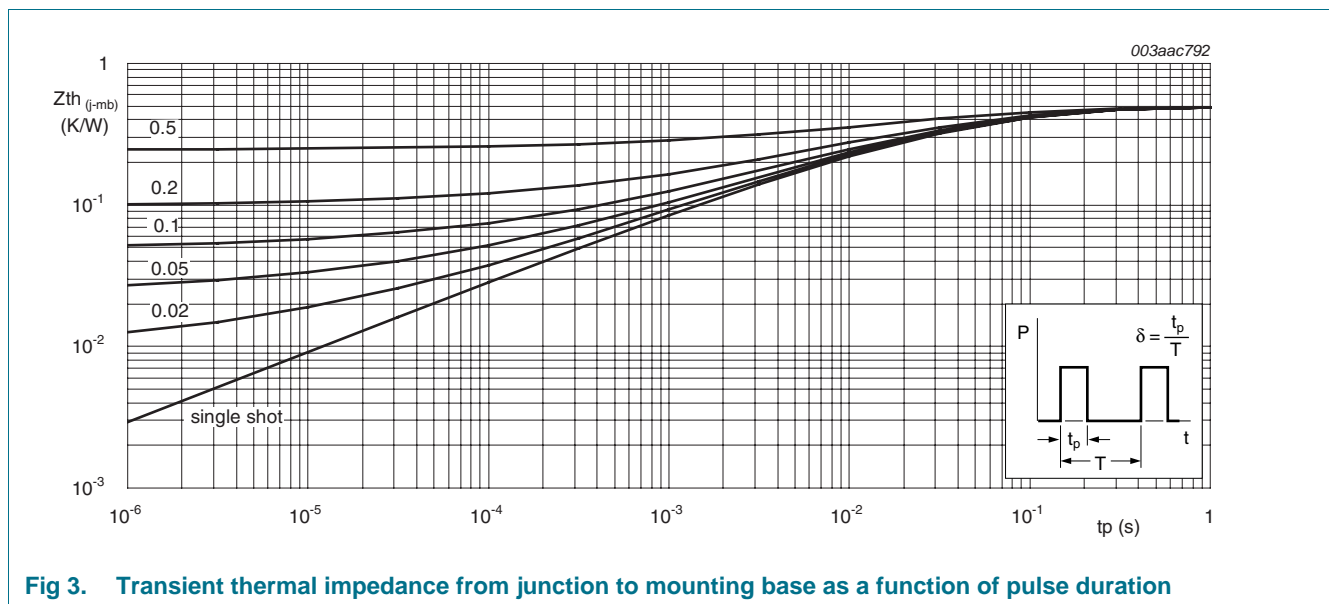
$$P_{der} = \frac{P_{tot}}{P_{tot(25^{\circ}C)}} \times 100\%$$

**Fig 2. Normalized total power dissipation as a function of mounting base temperature**

## 5. Thermal characteristics

**Table 5. Thermal characteristics**

Symbol	Parameter	Conditions	Min	Typ	Max	Unit
$R_{th(j-mb)}$	thermal resistance from junction to mounting base	see <a href="#">Figure 3</a>	-	-	0.57	K/W
$R_{th(j-a)}$	thermal resistance from junction to ambient	vertical in free air	-	60	-	K/W



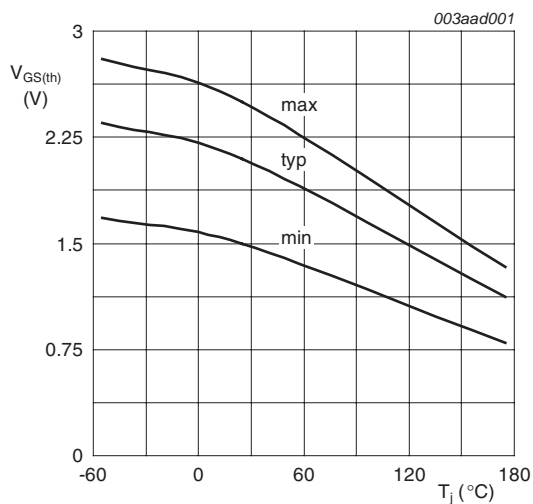
## 6. Characteristics

Table 6. Characteristics

Symbol	Parameter	Conditions	Min	Typ	Max	Unit
<b>Static characteristics</b>						
$V_{(BR)DSS}$	drain-source breakdown voltage	$I_D = 250 \mu A; V_{GS} = 0 V; T_j = 25 \text{ }^\circ\text{C}$	40	-	-	V
		$I_D = 250 \mu A; V_{GS} = 0 V; T_j = -55 \text{ }^\circ\text{C}$	36	-	-	V
$V_{GS(th)}$	gate-source threshold voltage	$I_D = 1 \text{ mA}; V_{DS} = V_{GS}; T_j = 25 \text{ }^\circ\text{C};$ see <a href="#">Figure 4</a>	1.5	2.1	2.5	V
		$I_D = 1 \text{ mA}; V_{DS} = V_{GS}; T_j = -55 \text{ }^\circ\text{C};$ see <a href="#">Figure 4</a>	-	-	2.8	V
		$I_D = 1 \text{ mA}; V_{DS} = V_{GS}; T_j = 175 \text{ }^\circ\text{C};$ see <a href="#">Figure 4</a>	0.8	-	-	V
$I_{DSS}$	drain leakage current	$V_{DS} = 40 V; V_{GS} = 0 V; T_j = 25 \text{ }^\circ\text{C}$	-	0.02	1	$\mu A$
		$V_{DS} = 40 V; V_{GS} = 0 V; T_j = 175 \text{ }^\circ\text{C}$	-	-	500	$\mu A$
$I_{GSS}$	gate leakage current	$V_{DS} = 0 V; V_{GS} = 20 V; T_j = 25 \text{ }^\circ\text{C}$	-	2	100	nA
		$V_{DS} = 0 V; V_{GS} = -20 V; T_j = 25 \text{ }^\circ\text{C}$	-	2	100	nA
$R_{DS(on)}$	drain-source on-state resistance	$V_{GS} = 10 V; I_D = 15 A; T_j = 25 \text{ }^\circ\text{C};$ see <a href="#">Figure 5</a>	-	2.2	2.6	m $\Omega$
		$V_{GS} = 5 V; I_D = 15 A; T_j = 25 \text{ }^\circ\text{C};$ see <a href="#">Figure 5</a>	-	[tbd]	[tbd]	m $\Omega$
		$V_{GS} = 4.5 V; I_D = 15 A; T_j = 25 \text{ }^\circ\text{C};$ see <a href="#">Figure 5</a>	-	[tbd]	[tbd]	m $\Omega$
		$V_{GS} = 10 V; I_D = 15 A; T_j = 175 \text{ }^\circ\text{C};$ see <a href="#">Figure 5</a>	-	-	5.4	m $\Omega$
<b>Dynamic characteristics</b>						
$Q_{G(tot)}$	total gate charge	$I_D = 25 A; V_{DS} = 32 V; V_{GS} = 10 V$	-	[tbd]	[tbd]	nC
		$I_D = 25 A; V_{DS} = 32 V; V_{GS} = 5 V$	-	[tbd]	[tbd]	nC
$Q_{GS}$	gate-source charge	$I_D = 25 A; V_{DS} = 32 V; V_{GS} = 10 V$	-	[tbd]	[tbd]	nC
$Q_{GD}$	gate-drain charge		-	[tbd]	[tbd]	nC
$C_{iss}$	input capacitance	$V_{GS} = 0 V; V_{DS} = 25 V; f = 1 \text{ MHz};$ $T_j = 25 \text{ }^\circ\text{C}$	-	[tbd]	[tbd]	pF
$C_{oss}$	output capacitance		-	[tbd]	[tbd]	pF
$C_{rss}$	reverse transfer capacitance		-	[tbd]	[tbd]	pF
$t_{d(on)}$	turn-on delay time	$V_{DS} = 30 V; R_L = 1.2 \text{ } \Omega; V_{GS} = 10 V;$ $R_{G(ext)} = 10 \text{ } \Omega$	-	[tbd]	[tbd]	ns
$t_r$	rise time		-	[tbd]	[tbd]	ns
$t_{d(off)}$	turn-off delay time		-	[tbd]	[tbd]	ns
$t_f$	fall time		-	[tbd]	[tbd]	ns
$L_D$	internal drain inductance	from contact screw on mounting base to centre of die ; $T_j = 25 \text{ }^\circ\text{C}$	-	3.5	-	nH
		from drain lead 6 mm from package to centre of die ; $T_j = 25 \text{ }^\circ\text{C}$	-	4.5	-	nH
$L_S$	internal source inductance	from source lead to source bond pad ; $T_j = 25 \text{ }^\circ\text{C}$	-	7.5	-	nH

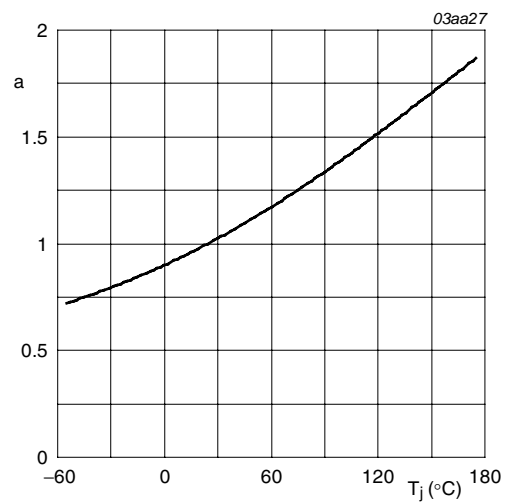
Table 6. Characteristics ...continued

Symbol	Parameter	Conditions	Min	Typ	Max	Unit
<b>Source-drain diode</b>						
$V_{SD}$	source-drain voltage	$I_S = 25 \text{ A}; V_{GS} = 0 \text{ V}; T_j = 25 \text{ }^\circ\text{C}$	-	0.85	1.2	V
$t_{rr}$	reverse recovery time	$I_S = 20 \text{ A}; dI_S/dt = -100 \text{ A}/\mu\text{s}; V_{GS} = 0 \text{ V}; V_{DS} = 25 \text{ V}$	-	[tbd]	[tbd]	ns
$Q_r$	recovered charge	$V_{GS} = 0 \text{ V}; V_{DS} = 25 \text{ V}$	-	[tbd]	[tbd]	nC



$$I_D = 1 \text{ mA}; V_{DS} = V_{GS}$$

Fig 4. Gate-source threshold voltage as a function of junction temperature



$$a = \frac{R_{DSon}}{R_{DSon(25^\circ\text{C})}}$$

Fig 5. Normalized drain-source on-state resistance factor as a function of junction temperature

**7. Package outline**

Plastic single-ended package; heatsink mounted; 1 mounting hole; 3-lead TO-220AB

SOT78

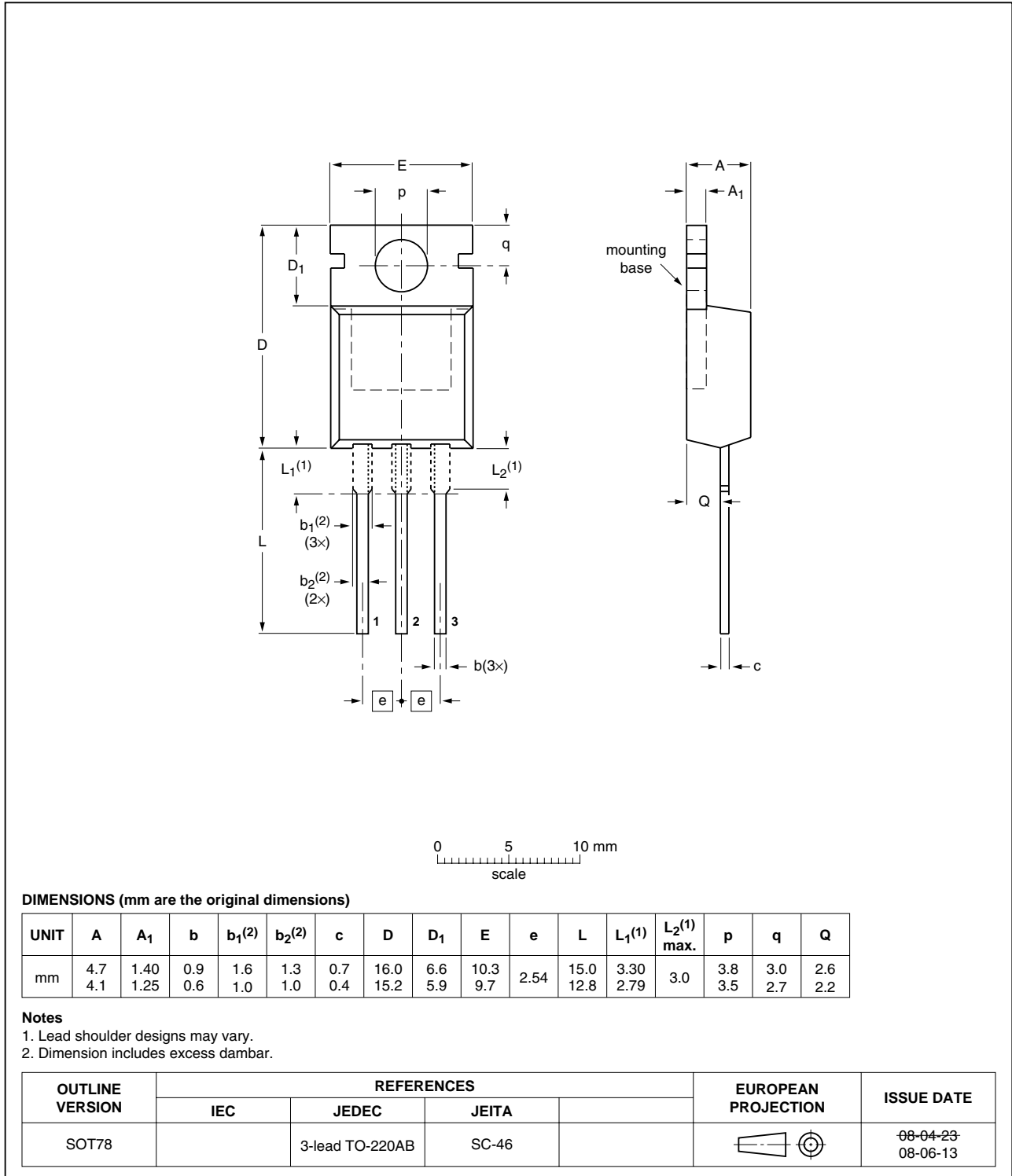


Fig 6. Package outline SOT78 (TO-220AB)



## 8. Revision history

Table 7. Revision history

Document ID	Release date	Data sheet status	Change notice	Supersedes
BUK652R6-40C v.1	20100705	Objective data sheet	-	-

## 9. Legal information

### 9.1 Data sheet status

Document status <sup>[1][2]</sup>	Product status <sup>[3]</sup>	Definition
Objective [short] data sheet	Development	This document contains data from the objective specification for product development.
Preliminary [short] data sheet	Qualification	This document contains data from the preliminary specification.
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